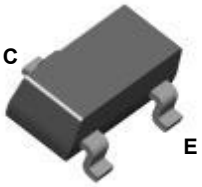
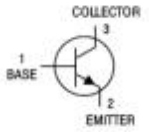
Silicon Epitaxial Planar Transistor(NPN)



SOT-23



Features

High Collector Current
Complementary To MMBT3906
Excellent HFE Linearity

Absolute Maximum Ratings*

T_A = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	40	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current -Continuous	200	mA
P_C	Collector Dissipation	200	mW
T_j, T_{stg}	Junction and Storage Temperature	-55~150	℃

Electrical Characteristics

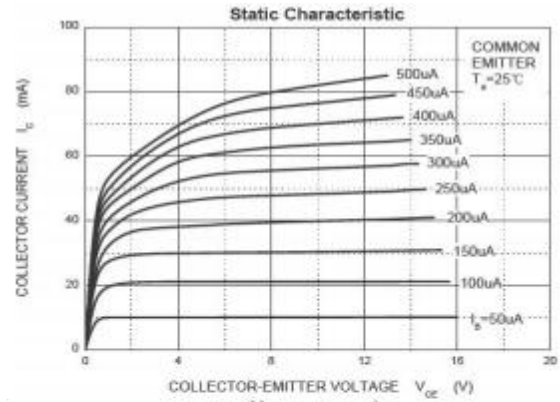
T_A = 25°C unless otherwise noted

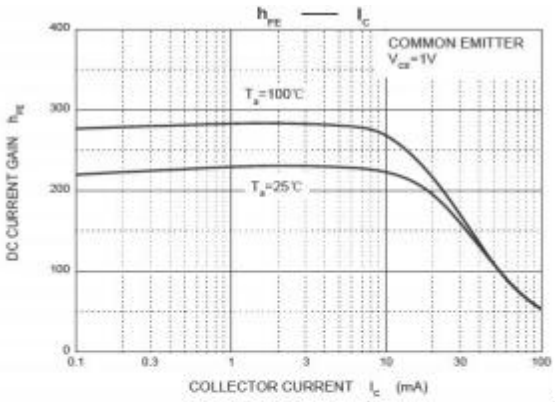
Parameter	Symbols	Test Condition	Min	Max	Unit
Collector-base breakdown voltage	**V(BR)CBO**	IC=10uA, IE=0	60		V
Collector-emitter breakdown voltage	**V(BR)CEO**	IC=1mA, IB=0	40		V
Emitter-base breakdown voltage	**V(BR)EBO**	IE=10uA, IC=0	6		V
Collector cut-off current	**ICEX**	VCE=30V, VEB(off)=3V		50	nA
Collector cut-off current	**ICBO**	VCB=60V, IE=0		100	nA
Emitter cut-off current	**IEBO**	VEB=5V, IC=0		100	nA
DC current gain	hFE(1) hFE(2) hFE(3)	VCE=1V, IC=10mA VCE=1V, IC=50mA VCE=1V, IC=100mA	100 60 30	300	
Collector-emitter saturation voltage	**VCE(sat)**	IC=50mA, IB=5mA		0 30	V
Base -emitter saturation voltage	**VBE(sat)**	IC=50mA, IB=5mA		0.95	V
Transition frequency	**fT**	VCE=20V, IC=10mA,f=100MHz	300		MHz
Delay time	td	VCC=3V, VBE(off)=-0.5V, IC=10mA, IB1=1mA		35	nS
Rise time	tr	VCC=3V, VBE(off)=-0.5V, IC=10mA, IB1=1mA		35	nS
Storage time	ts	VCC=3V, IC=10mA, IB1=IB2=1mA		200	nS
Fall time	tf	VCC=3V, IC=10mA, IB1=IB2=1mA		50	nS

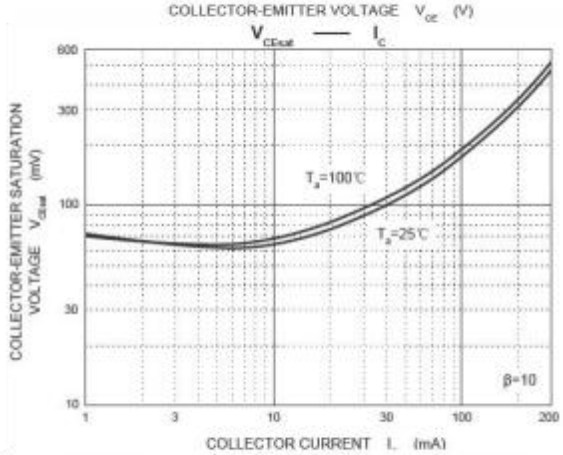
Device Information

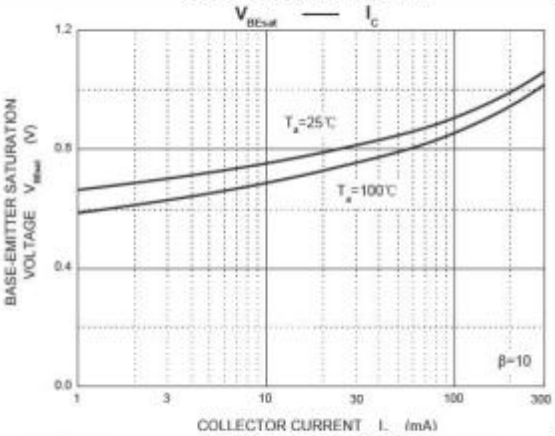
Type	MMBT3904
Marking	1AM
HFE	100-300

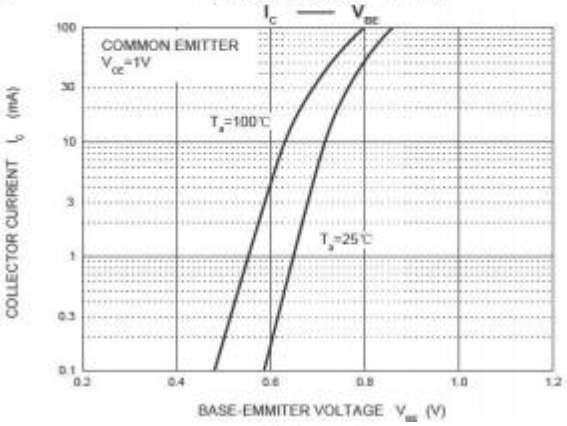
Typical Characteristics

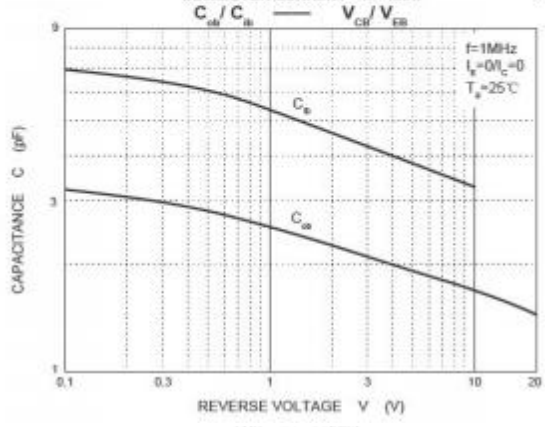


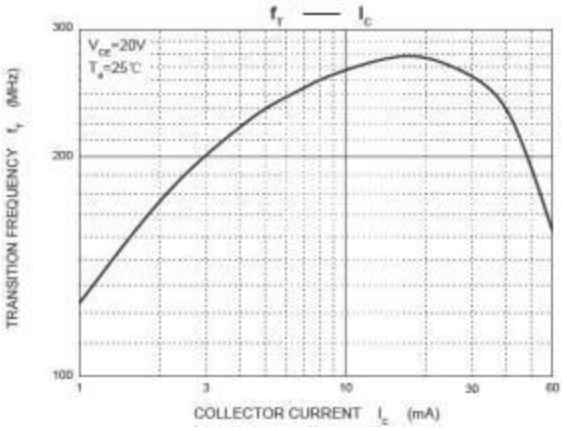


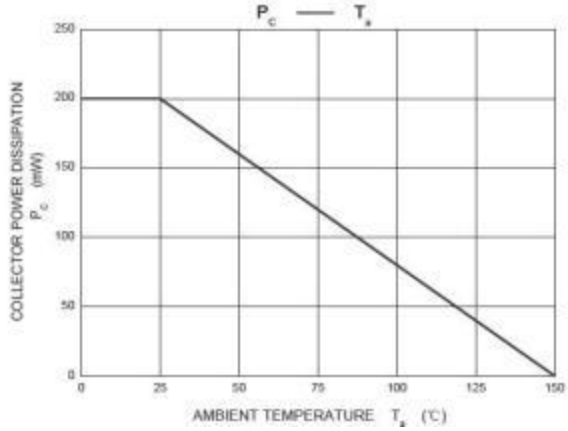






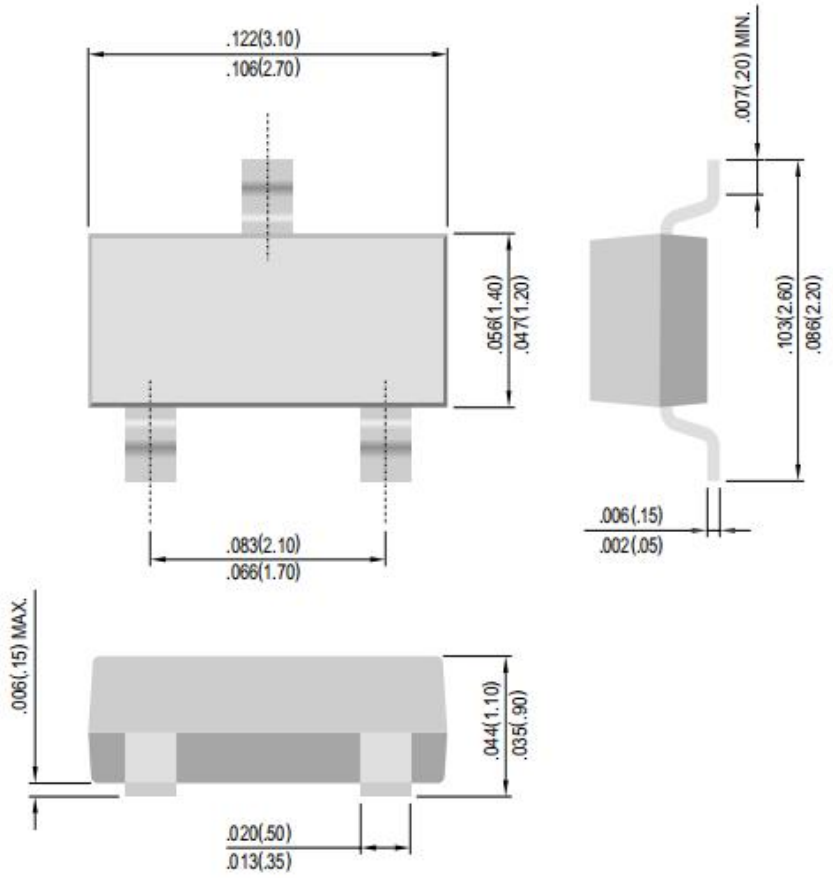






OUTLINE DRAWING

SOT-23



Website: http://www.jksemi.com
For additional information, please contact your local Sales Representative.
©Copyright 2016, jksemi
JKSEMI 金开盛电子 is a registered trademark of jksemi All rights are reserved